L Number	Hits	Search Text	DB	Time stamp]
-	25	("20010015446" "20020017696" "20020066908"		420066067972140071	"47
			US-PGPUB		
-	13	(HEMT or (High near Electron near Mobility	USPAT;	2004/06/04 11:51	
		near Transistor)) and (AlGaN and SiN and	US-PGPUB;		
	1	ohmic)	EPO; JPO;		
			DERWENT;		
			IBM_TDB		
	3938	'	USPĀT;	2004/06/04 11:51	
		near Transistor))	US-PGPUB;		ł
			EPO; JPO;		l
			DERWENT;	1	ŀ
-	140	//IIIIMI	IBM_TDB		
	142		USPAT;	2004/06/04 11:52	
		Mobility near Transistor))) and (carbide)	US-PGPUB;		
	-		EPO; JPO;		
			DERWENT;		
	259	//UEME on /Wish near District	IBM_TDB	0004/05/05 44 05	
	239		USPAT;	2004/06/07 14:26	
		Mobility near Transistor))) and (carbide	US-PGPUB;		
		or SiC)	EPO; JPO;		
			DERWENT;		
	2	(AlGaN) near channel and HEMT	IBM_TDB	0004/06/06 11 06	
	2	(Algan) hear channel and HEMT	USPAT;	2004/06/06 11:36	
			US-PGPUB;		
			EPO; JPO;		
			DERWENT;		
_	335	HEMT and ((lift near off) or "lift-off")	<pre>IBM_TDB USPAT;</pre>	2004/06/07 15:01	
	555	ment and ((IIIC hear off) of life-off)	US-PGPUB;	2004/06/07 15:21	
		•	EPO; JPO;	ļ	
			DERWENT;		
			IBM TDB		
-	2	HEMT and (conductive near mask)	USPAT;	2004/06/07 15:21	
	_	The state of the s	US-PGPUB;	2004/00/07 15.21	
			EPO; JPO;		
			DERWENT;		
			IBM TDB		ŀ
-	802	(conductive near mask) and semiconductor	USPAT;	2004/06/07 15:24	
			US-PGPUB;	,,,	
			EPO; JPO;		
			DERWENT;		
			IBM TDB		
-	393	((conductive near mask) and semiconductor	USPĀT;	2004/06/07 15:23	
) and transistor .	US-PGPUB;		
			EPO; JPO;		
			DERWENT;		
	.		IBM_TDB		
-	15	(((aluminum near nitride) or AlN) near	USPAT;	2004/06/07 15:24	
	.	mask) and semiconductor	US-PGPUB;		
	<u> </u>		EPO; JPO;		
			DERWENT;		
		(#6540000W) ===	IBM_TDB		
_	2	("6548333").PN.	USPAT;	2004/09/16 15:25	
			US-PGPUB;		
			EPO; JPO;		
			DERWENT;		
			IBM_TDB		